





TO-220 Plastic Package

BUX84, BUX84A

NPN PLASTIC POWER TRANSISTORS BUX84. 84A

PIN CONFIGURATION 1. BASE 2. COLLECTOR

K

M

N

0

12.70 2.80

2.03

MAX.

16.51

10.67

4.83

0.90

1.40

3.88

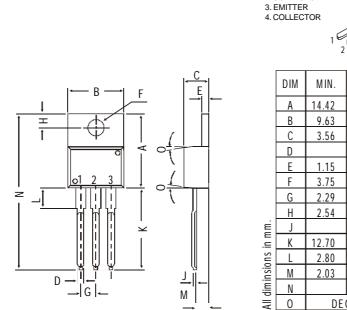
0.56

4.07

31.24

DEG 7

High Voltage, High Speed Power Switching Applications



ABSOLUTE MAXIMUM RATINGS

		84	84 A	l
Collector-emitter voltage ($V_{BE} = 0$)	$V_{C\!E\!S}$	max. 800	800	V
Collector-emitter voltage (open base)	$V_{C\!E\!O}$	max. 400	400	V
Collector current	I_C	max.	2.0	\boldsymbol{A}
Total power dissipation up to $T_C = 25^{\circ}C$	P_{tot}	max.	40	W
Junction temperature	T_{j}	max.	<i>150</i>	${}^{\!$
Collector-emitter saturation voltage	· ·			
$I_C = 0.3A$; $I_B = 30 \text{ mA}$	V_{CEsat}	max. 1.5	0.8	8 V
D.C. current gain				
$I_C = 0.1 \; A; \; V_{CE} = 5 \; V$	$h_{\!F\!E}$	min.	<i>30</i>	

RATINGS (at T_A =25°C unless otherwise specified) Limiting values

		04	04/	1
Collector-emitter voltage ($V_{BE} = 0$)	$V_{C\!E\!S}$	max. 800	80	0 V
Collector-emitter voltage (open base)	$V_{C\!E\!O}$	max. 400	40	0 V
Emitter-base voltage (open collector)	V_{EBO}	max.	5.0	V

Collector current	I_C	max.	2.0	A
Collector current (Peak value)	I_{CM}	max.	3.0	\boldsymbol{A}
Base current	I_B	max.	0.75	A
Total power dissipation up to $T_C = 25^{\circ}C$	P_{tot}	max.	40	W
Junction temperature	T_j	max.	150	${}^{\!$
Storage temperature	T_{stg}		−65 to +15	0 C
THERMAL RESISTANCE				
From junction to case	R_{thj-c}	=	3.125	CW
CHARACTERISTICS				
$T_{amb} = 25^{\circ}C$ unless otherwise specified				
			84 84	\boldsymbol{A}
Collector cutoff current				
$V_{BE} = 0$; $V_{CE} = Rated V_{CES}$	I_{CES}	max.	0.2	mA
$V_{BE} = 0$; $V_{CE} = Rated V_{CES}$; $T_C = 125$ °C	I_{CES}	max.	1.5	mA
Emitter cut-off current				
$I_C = 0; V_{EB} = 5V$	I_{EBO}	max.	1.0	mA
Breakdown voltages				
$I_C = 100 \text{ mA}; I_B = 0$	$V_{CEO(sus)}^*$	min.	400	V
$I_C = 1 \text{ mA}; V_{BE} = 0$	$V_{C\!E\!S}$	min.	800	V
$I_E = 1 \text{ mA}; I_C = 0$	V_{EBO}	min.	5.0	V
Saturation voltages				
$I_C = 0.3 A; I_B = 30 mA$	V_{CEsat}^*	max.	1.5 0.	8 V
$I_C = 1 A; I_B = 0.2 A$	V_{CEsat}^*	max.	3.0 1.	0 V
	V_{BEsat}^*	max.	1.1	V
D.C. current gain				
$I_C = 0.1 A; V_{CE} = 5 V$	$h_{\!F\!E}^*$	min.	30	
Transition frequency $f = 1 MHz$				
$I_C = 0.2 \; A; \; V_{CE} = 10 \; V$	f_T	typ.	20	MHz
Switching time				
$I_C = 1A$; $V_{CC} = 250V$				
$I_B = 0.2A$; $-I_B = 0.4A$				
Turn on time	t _{on}	max	0.5	μs
Storage time	t_S	max.	3.5	μs
Fall time	t_f	max.	1.4	μs
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^{*} Pulsed: pulse duration = 300 μ s; duty cycle \leq 2%.

Notes

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished on the CDIL Web Site/CD is believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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